Nanophotonic integrated circuits with 1.5% single-photon nonlinearity

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Optical nonlinearity plays a pivotal role in quantum information processing using photons, from heralded single-photon sources to long-sought quantum repeaters. Despite the strong light-atom interaction, an all-optical single-photon nonlinearity is highly desired for more scalable quantum protocols. Here, we realize nanophotonic integrated circuits in thin-film InGaP with a record-high second-order optical nonlinearity of 1.5%, measured by the ratio of the single-photon trimodal coupling rate (g/2π = 11.2 MHz) and intrinsic cavity photon loss rate. Bulk optical nonlinearity at this level will enable high-efficiency non-classical light sources on microchips and quantum information processing using bosonic modes.

I. INTRODUCTION

Optical nonlinearity is indispensable for a number of quantum information protocols using photons. Deterministic quantum logic gates can be realized when the photon-photon interaction strength exceeds the photon loss rate, for example, via cavity-QED systems. Surprisingly, weak optical nonlinearity associated with bulk nonlinear susceptibilities might enable alternative protocols for quantum communication and computation, besides its wide use for (heralded) single-photon generation. For example, when accompanied with ancillary coherent states, weak optical nonlinearity might enable quantum non-demolition measurement of flying photons, which is useful for relaying quantum information [1,3]. Moreover, continuous-variable cluster states synthesized from the squeezed vacuum have been proposed to implement fault-tolerant quantum computing when the squeezing level exceeds certain thresholds [4,6]. These protocols, while avoiding the demanding light-atom interface, still need an optical nonlinearity beyond those typically achievable with bulk crystals.

One method to enhance photon-photon interaction via bulk nonlinearity is to make optical microcavities such that photons confined in wavelength-scale cavities interact accumulatively throughout their lifetime. The key to this approach is a thin-film material platform that yields, simultaneously, large nonlinear mode coupling and low optical losses. In particular, photonic integrated circuits have been developed in a growing number of thin-film materials with substantial second-order nonlinear susceptibility, such as gallium arsenide (GaAs) [7,8] and aluminum gallium arsinite [9,10]. However, these III-V materials are associated with intrinsic optical losses due to, for example, two-photon or sub-bandgap absorption at near-infrared wavelengths [11], limiting their use in quantum optics. Recently, wide bandgap materials, including aluminum nitride [12,13] and lithium niobate [14,17], are emerging among the leading nonlinear photonic platforms. With microcavities of ultrahigh quality factors, these material systems have yielded second-harmonic generation with unprecedented efficiency [10] and ultra-bright single-photon sources [17]. Ultimately, though, they might still be limited by a mediocre second-order nonlinear susceptibility that is one to two orders smaller than the non-nitride III-V materials.

Here, we explore another III-V material, indium gallium phosphide (InGaP), and demonstrate record-high all-optical single-photon nonlinearity. InGaP has a large second-order nonlinear susceptibility (χ(2) ≈ 220 pm/V [15]), comparable to GaAs, and a sizable bandgap of about 1.9 eV which suppresses two-photon absorption at telecom wavelengths. Previous studies of InGaP nonlinear photonics focuses on using its Kerr nonlinearity in waveguides and photonic crystal cavities for frequency combs and optical parametric oscillators [19,20]. We explore the substantial second-order nonlinearity in thin-film InGaP and realize high-Q quasi-phase-matched microring resonators with strongly coupled 1550 nm and 775 nm wavelength modes. Via second-harmonic generation, we inferred a single-photon nonlinearity of 1.5%, characterized by the ratio between the single-photon mode coupling coefficient and intrinsic cavity loss rate, which is the highest among all demonstrated nonlinear photonic platforms. Such single-photon nonlinearity might enable breakthroughs including the generation of single-mode strongly squeezed states on microchips and quantum non-demolition measurement of photons all-optically.

II. DEVICE DESIGN AND SIMULATION

The devices we made in this study are waveguide-coupled doubly-resonant microring resonators. The mi-
croting resonator supports fundamental 1550 nm and second-harmonic 775 nm resonances coupled via the second-order optical nonlinearity. The interaction between the two resonances can be described by the following Hamiltonian,
\[ \hat{H} = \hbar (\hat{a}^{\dagger} \hat{b} + \hat{b}^{\dagger} \hat{a}) , \]
where \( \hat{a}(\hat{a}^{\dagger}) \) and \( \hat{b}(\hat{b}^{\dagger}) \) are the annihilation(creation) operators for the fundamental and second-harmonic resonance, respectively, and \( g \) is the single-photon mode coupling coefficient. For disordered InGaP used in this study with a zinc blende crystal structure, its second-order nonlinear optical susceptibility only has the component \( \chi^{(2)}_{xyz} \), leading to a mode coupling coefficient given by
\[ g = \sqrt{\frac{\hbar \omega_{a} \omega_{b}}{8 \varepsilon_{0}}} \int \frac{d\mathbf{r}_{a} \chi^{(2)}_{xyz}}{[E_{a}]^{2} \sqrt{\int d\mathbf{r}_{b}|E_{b}|^{2}}} . \]
where \( \omega_{a(b)} \) is the angular frequency of resonance \( a(b) \), \( E_{a(b)} \) is the modal electric field, \( \varepsilon_{0} \) is the vacuum permittivity, and \( \varepsilon_{a(b)} \) is the relative permittivity at 1550 nm (775 nm). We also define the \( z \)-direction to be perpendicular to the device plane.

To optimize \( g \) and thus the device-level nonlinearity, modes \( a \) and \( b \) need to be phase-matched and have substantial field overlap defined by the intermodal integral in Eq. 2. We choose the fundamental transverse-electric mode (TE\(_{00}\)) and fundamental transverse-magnetic mode (TM\(_{00}\)) for the 1550 nm and 775 nm resonances (Fig. 1b), respectively, taking advantage of their dominant in-plane (for TE\(_{00}\)) and out-of-plane (for TM\(_{00}\)) electric field components. The \( \chi^{(2)}_{xyz} \) nonlinear susceptibility also imposes a quasi-phase-matching condition between the two traveling-wave resonances for maximal coupling (Appendix A), i.e.,
\[ 2\omega_{a} = \omega_{b} , \quad |2m_{a} - m_{b}| = 2 , \]
where \( m_{a(b)} \) is the azimuthal number of resonance \( a(b) \).

Because of the strong dispersion of InGaP with a refractive index of \( n = 3.12 \) at 1550 nm and \( n = 3.41 \) at 775 nm [22], we find the quasi-phase-matching condition can only be satisfied in thin InGaP microrings with a high-aspect-ratio cross section. Fig. 1b plots the frequency of the TE\(_{00}\) mode with \( m_{a} = 36 \) and the TM\(_{00}\) modes with \( m_{b} = 2m_{a} \pm 2 \) for the 115 nm thick microring with different width and a center radius \( R = 5 \mu m \). The intercept points of the dispersion curves thus yield the ring width, around 945 nm and 1360 nm, respectively, satisfying the quasi-phase-matching condition given by Eq. 3. In the simulated structure, we also included a thin layer (50 nm) of silicon dioxide covering the suspended InGaP microring, in accordance with the fabricated device (see Section III). We select the thickness of the InGaP film to be 115 nm because for film thickness over 120 nm the phase-matching condition cannot be realized and for thinner InGaP the cavity mode will be less confined, leading to lower quality factor and coupling strength of cavity resonances. Using \( \chi^{(2)}_{xyz} = 220 \) pm/V [18], we numerically find a coupling coefficient \( g/2\pi = 10.90(5.96) \) MHz between the 1550 nm TE\(_{00}\) and 775 nm TM\(_{00}\) resonances of the 5 \( \mu m \) microring satisfying the phase-matching condition of \( m_{b} = 2m_{a} + 2 \) (\( m_{b} = 2m_{a} - 2 \)). It is worth noting that \( g \) scales approximately as \( R^{-0.5} \) and thus smaller microring resonators will yield larger nonlinear coupling, though photon lifetimes might decrease due to excess bending losses. Fig. 1 reveals that the quasi-phase-matching condition is extremely sensitive to the thickness of InGaP films, imposing stringent constraints on the thickness uniformity of the fabricated InGaP film for realizing optimized devices.

FIG. 1. a. Schematic plot of a \( \chi^{(2)} \) microring resonator. Inset shows the electric field of the 1550 nm TE\(_{00}\) resonance (\( E_{r} \) component) and 775 nm TM\(_{00}\) resonance (\( E_{z} \) component) at the cross section of the microring. b. Dispersion curve of the fundamental mode with azimuthal number \( m_{a} = 36 \) and second-harmonic modes with azimuthal number \( m_{b} = 2m_{a} \pm 2 \). The microring has thickness of 115 nm and \( R = 5 \mu m \). c. The width of the microring satisfying the phase-matching condition \( m_{b} = 2m_{a} + 2 \) between the 1550 nm and 775 nm resonances.

### III. DEVICE FABRICATION

The devices are fabricated from 115 nm thick disordered InGaP thin films grown on the GaAs substrate by metal-organic chemical vapor deposition. The surface roughness of the InGaP thin film is about 0.32 nm measured by atomic-force microscopy (AFM) (Fig. 2a). The device pattern is defined using 150 keV electron beam lithography and negative tone resist hydrousilsesquioxane (HSQ). A 20 nm thick layer of silicon dioxide is deposited on InGaP to enhance the adhesion of HSQ. The
pattern is transferred to InGaP via inductively coupled plasma reactive-ion etch (ICP-RIE) using Cl₂/CH₄/Ar gas mixture. After a short buffered oxide etch to remove the residual oxide, a layer of 50 nm thick silicon dioxide is deposited on the chip via atomic layer deposition. A second electron beam lithography and subsequent ICP-RIE using CHF₃ gas are applied to pattern etch-through holes in the silicon dioxide layer for undercut of the InGaP device. Finally, the InGaP device is released from the GaAs substrate using citric acid-based selective etching [23]. The suspended InGaP device is mechanically anchored to the silicon dioxide membrane.

![Surface morphology of the 115 nm thick InGaP-on-GaAs film in a 2 μm by 2 μm region measured by AFM.](image)

**FIG. 2.** a. Surface morphology of the 115 nm thick InGaP-on-GaAs film in a 2 μm by 2 μm region measured by AFM. The root mean square (RMS) of the surface roughness is 0.32 nm. b. Scanning electron microscopy image of the fabricated device and schematic of the measurement setup. Second harmonic generation is measured via the solid path while the transmission spectrum is measured via the same-color path. IR: infrared, FPC: fiber polarization controller, PD: photodetector. c. Scanning electron microscopy images of the waveguide-coupled microring resonator.

![Scanning electron microscopy images of the waveguide-coupled microring resonator.](image)

The transmission spectrum of the microring resonator is measured using two tapered fibers evanescently coupled to the waveguide couplers. The measured coupling efficiency (unoptimized) is about 60% and 33% for the 1550 nm TE-polarized and 775 nm TM-polarized light, respectively. Fig. 3 shows the transmission spectrum of a 5 μm-radius microring, where the 1550 nm band TE₀₀ and 775 nm band TM₀₀,₁₀,₂₀,₃₀ resonances are observed. By fitting the transmission coefficient using the input-output formula, we inferred the intrinsic quality factor of the 1550 nm TE₀₀ and 775 nm TM₀₀ resonances to be around 2.5×10⁵ and 10⁵, respectively. We also measured the quality factor of the 1550 nm band TE₀₀ resonances of 20 μm- and 80 μm-radius microrings, which is shown in Fig. 3. The similarity of the intrinsic quality factor of microrings with different sizes indicates the dominant optical loss is likely due to the surface roughness of InGaP films instead of the etched sidewall or waveguide bending.

We then measured the nonlinear mode coupling $g$ via second-harmonic generation (SHG) in a quasi-phase-matched 5 μm-radius microring resonator. Due to fabrication imperfection, the frequencies of a pair of phase-matched resonances might be slightly detuned, i.e., $\omega_b - 2\omega_a \neq 0$. We used an external heater to adjust the frequency detuning of the two resonances, thanks to their different thermo-optic responses, roughly 0.04 nm/C° and 0.017 nm/C° for the 1550 nm TE₀₀ and 775 nm TM₀₀ resonances, respectively. Fig. 3 shows the spectrum of a pair of frequency-matched 1550 nm and 775 nm resonances satisfying the condition of $m_{b, e} = 2m_{a, e} + 1$. Due to surface roughness induced backscattering, the degenerate clockwise and counter-clockwise traveling-wave resonances hybridize and split into standing-wave resonances that are equal superpositions of the two.

In the pump non-depletion region, the normalized SHG efficiency, $\eta \equiv g_{\text{eff}}^2 \omega_p^2$, where $g_{\text{eff}}$ and $\omega_p$ are the on-chip SHG and pump power, respectively, for the standing-wave resonances is given by [24] (Appendix A)

$$\eta = \frac{g^2}{2} \frac{\kappa_{b,e}/2}{\Delta_2^2 + (\kappa_b/2)^2} \left( \frac{\kappa_{a,e}/2}{\Delta_a^2 + (\kappa_a/2)^2} \right)^2 \frac{\hbar \omega_b}{(\hbar \omega_p)^2},$$

where $\kappa_{a,b,e} = \kappa_{a,b,e} + \kappa_{a,b,e}$ are the total, external and intrinsic photon (energy) loss rate of the resonances, respectively, $\Delta_a = \omega_a - \omega_p$, $\Delta_b = \omega_b - 2\omega_p$, and $\omega_p$ is the frequency of the pump. We note the fact that the photon loss rate is roughly the same for
FIG. 3. a. The transmission spectrum of a 5 µm-radius microring in the 1550 nm TE and 775 nm TM band. b. The intrinsic quality factor of 1550 nm TE00 resonances of microrings with different radius. The error bar represents the standard deviation of the quality factor. c. Normalized transmission spectrum of a pair of phase-matched fundamental and second harmonic resonances (highlighted by the dashed line), corresponding to the boxed resonances in a. The split resonances are due to surface roughness induced backscattering. d. SHG signal for various pump power (color-coded with the corresponding peak power given in e). e. Peak SHG power (subtracted with the background) versus pump power. The line fitted to the colored data points illustrates the quadratic relationship between the SHG and pump power.

We define a figure-of-merit, $g/κ_{a,i}$, to characterize the strength of single-photon nonlinearity of the doubly-resonant cavity. This figure-of-merit is directly related to, for example, the rate of photon-pair generation via spontaneous parametric down conversion [12] and the two-photon scattering amplitude [27]. The InGaP microring resonator of this work yields a single-photon nonlinearity of $1.52 ± 0.11\%$, which is the highest among all demonstrated nonlinear photonic platforms (Fig. 4).
Despite the high quality factor of fabricated microring resonators, the strong single-photon nonlinearity is attributed to the large \( \chi^{(2)} \) coefficient of InGaP, which is one to two orders larger than other nonlinear materials including lithium niobate and aluminum nitride.

V. DISCUSSION

In summary, we have developed nanophotonic integrated circuits in InGaP thin films with record-breaking second-order optical nonlinearity, while avoiding the fabrication complications such as periodic poling associated with lithium niobate. While the suspended device here is suitable for few-photon applications, using the wafer bonding technique [28], the InGaP-on-substrate system with a large heat capacity instead can be used for applications involving more optical power. There is still room to further enhance the effective optical nonlinearity in the InGaP platform, for example, by making more compact micro-resonators and improving the mode quality factor. The measured quality factor is likely to be limited by the surface roughness of the epitaxial InGaP film—given the high aspect-ratio of the cross-section of the micro-resonator—which is still 2–3 times larger than typical silicon-on-insulator wafers. Tuning the material growth condition or using post-growth polishing methods [29] might help further reducing the surface roughness.

The strong single-photon nonlinearity demonstrated in this work will lead to unprecedented non-classical light sources on microchips, including single-mode strongly squeezed states, and quantum information processing using bosonic modes. Ultimately, the InGaP platform, when combined with other compatible III-V materials [30, 31], is promising for realizing a full-fledged quantum photonic microchip with integrated lasers, photodetectors, linear and nonlinear device components.

Appendix A: Derivation of the quasi-phase-matching condition

According to Ref. [27], the \( \chi^{(2)} \)-mediated nonlinear mode coupling between two resonances is given by

\[
g = \sqrt{\frac{\hbar \omega_0^2 \omega}{8\epsilon_0}} \int \frac{d\mathbf{r}}{d \epsilon_{\alpha\beta} |E_{\alpha}|^2} \sqrt{\int d\mathbf{r} \epsilon_{\alpha\beta} |E_{\beta}|^2}.
\] (A1)

Applying it to the disordered InGaP with only \( \chi^{(2)}_{xyz} \) component, we have

\[
g = \sqrt{\frac{\hbar \omega_0^2 \omega}{8\epsilon_0}} \int \frac{d\mathbf{r}}{d \epsilon_{\alpha\beta} |E_{\alpha}|^2} \sqrt{\int d\mathbf{r} \epsilon_{\alpha\beta} |E_{\beta}|^2}.
\] (A2)

To find the phase-matching condition for the traveling-wave resonances, we write the electric field in the cylindrical coordinate using the transformation

\[
E_{ax} = (E_{at} \cos \theta - E_{bt} \sin \theta) e^{-im_{\theta}},
\]
\[
E_{xy} = (E_{at} \sin \theta + E_{bt} \cos \theta) e^{-im_{\theta}},
\] (A3)

where \( s = a, b \). We consider only one of the terms in the numerator of Eq. A2 i.e.,

\[
\int d\mathbf{r} \chi^{(2)}_{xyz} E_{ax}^* E_{ay} E_{bz}
\]

\[
= \frac{1}{4} \int d\mathbf{r} \chi^{(2)}_{xyz} \left[ (2E_{at}^* E_{\theta} - i(E_{at}^2 - E_{2\theta}^2)) E_{bz} e^{i(2m_{\theta} - m_{b} + 2)\theta} + (2E_{at}^* E_{\theta} + i(E_{at}^2 - E_{2\theta}^2)) E_{bz} e^{i(2m_{\theta} - m_{b} - 2)\theta} \right].
\] (A4)

This integral is nonzero only when

\[
2m_{a} - m_{b} = \pm 2.
\] (A5)

Other terms in Eq. A2 lead to the same result given the non-identical indices in the sum.

When both modes are standing-wave resonances, i.e., even and odd mixtures of the traveling-wave resonances, their mutual coupling \( g' \) can be derived as follows. Note \( g \) above can be chosen to be real, thus if the second-harmonic mode is even, i.e., \( E_{0} = (E_{b} + E_{0})/\sqrt{2} \), we have, regardless of the symmetry of the fundamental mode,

\[
g' = \sqrt{\frac{\hbar \omega_0^2 \omega}{8\epsilon_0}} \int \frac{d\mathbf{r}}{d \epsilon_{\alpha\beta} |E_{\alpha}|^2} \sqrt{\int d\mathbf{r} \epsilon_{\alpha\beta} |E_{\beta}|^2}
\]

\[
= \sqrt{\frac{\hbar \omega_0^2 \omega}{64\epsilon_0}} \int \frac{d\mathbf{r}}{d \epsilon_{\alpha\beta} |E_{\alpha}|^2} \sqrt{\int d\mathbf{r} \epsilon_{\alpha\beta} |E_{\beta}|^2}
\]

\[
= \frac{1}{\sqrt{2}} g,
\] (A6)

where only terms satisfying Eq. [A3] are kept. On the other hand, if the second-harmonic mode is odd, i.e., \( E_{0} = (E_{b} - E_{0})/\sqrt{2} \), the coupling between the two standing-wave resonances is zero. Thus, following Ref. [24], the formula for SHG efficiency is given by Eq. 4 after taking into account the fact that the one-side cavity-to-waveguide loss rate is \( \kappa_{e}/2 \) for standing-wave resonances. We stress the loss rate defined in Ref. [24] is half of the cavity photon (energy) loss rate used here. The normalized transmission spectrum of split resonances is fitted using the following formula to extract the loss rate:

\[
T[\omega] = \left| 1 - \frac{\kappa_{e,even}/2}{\kappa_{even}/2 - i(\omega - \omega_{even})} - \frac{\kappa_{e,odd}/2}{\kappa_{odd}/2 - i(\omega - \omega_{odd})} \right|^2.
\] (A7)


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